



Fig. 1

[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION AMORPHOUS (A) PLASMA]-[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (B) PLASMA]-[PLASMA DOPING (B) PLASMA]

Fig. 2

[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION AMORPHOUS (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION OF AMORPHOUS (A) PLASMA, BIAS POWER LOW SITUATION]-[PLASMA DOPING (B) PLASMA, BIAS POWER LOW SITUATION]-[PLASMA DOPING (B) PLASMA]

Fig. 3

[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION AMORPHOUS (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION OF AMORPHOUS (A) PLASMA, PRESSURE HIGH SITUATION]-[PLASMA DOPING (B) PLASMA, PRESSURE HIGH SITUATION]-[PLASMA DOPING (B) PLASMA]

Fig. 4

[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (B) PLASMA]-[PLASMA DOPING (B) PLASMA]-[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION OF AMORPHOUS (A) PLASMA]

Fig. 5

[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION AMORPHOUS (A) PLASMA]-[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (B) PLASMA]-[PLASMA DOPING (B) PLASMA]-[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (C) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION OF AMORPHOUS (C) PLASMA]

Fig. 6

[MATCHING POINT INITIAL CONDITION IS SET TO ONE FOR USE IN (A) PLASMA]-[PLASMA IRRADIATION FOR REALIZATION AMORPHOUS (A) PLASMA]-[PLASMA DOPING (B) PLASMA]

Fig. 7

